

isc Silicon NPN Power Transistor

2SD855

DESCRIPTION

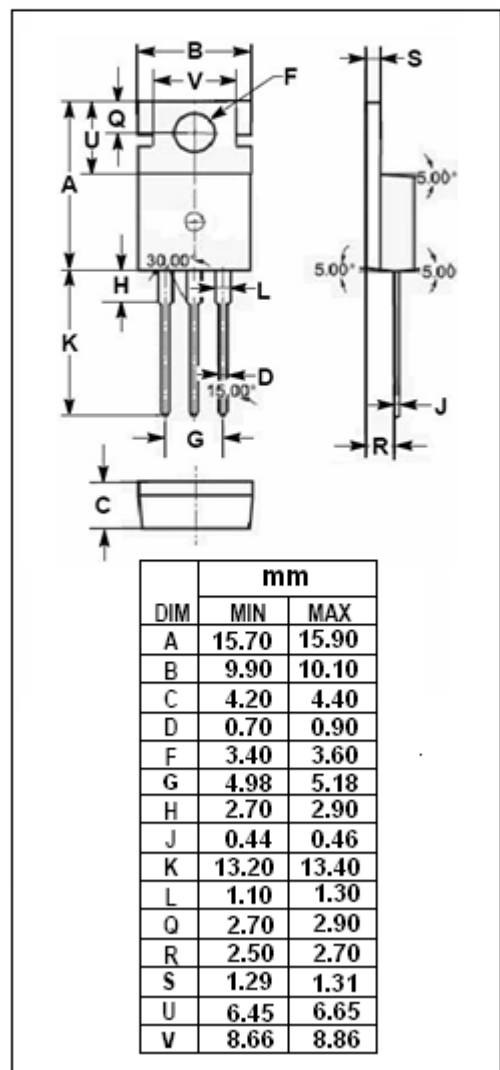
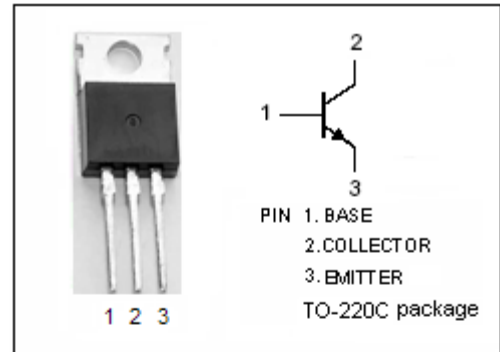
- Collector-Emitter Breakdown Voltage-  
:  $V_{(BR)CEO} = 60V(\text{Min})$
- Good Linearity of  $h_{FE}$
- Wide Area of Safe Operation
- Complement to Type 2SB760

APPLICATIONS

- Medium power amplifier applications.

ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	60	V
$V_{CEO}$	Collector-Emitter Voltage	60	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current-Continuous	1	A
$I_{CM}$	Collector Current-Peak	2	A
$P_C$	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	30	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$



**isc Silicon NPN Power Transistor****2SD855****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=30\text{mA}; I_B=0$	60			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=1\text{A}; I_B=0.125\text{A}$			1.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C=1\text{A}; V_{CE}=4\text{V}$			1.3	V
$I_{CEO}$	Collector Cutoff Current	$V_{CE}=60\text{V}; I_B=0$			300	$\mu\text{A}$
$I_{CES}$	Collector Cutoff Current	$V_{CE}=80\text{V}; I_E=0$			200	$\mu\text{A}$
$I_{EBO}$	Emitter Cutoff Current	$V_{EB}=5\text{V}; I_C=0$			1	mA
$h_{FE-1}$	DC Current Gain	$I_C=0.2\text{A}; V_{CE}=4\text{V}$	40		450	
$h_{FE-2}$	DC Current Gain	$I_C=1\text{A}; V_{CE}=4\text{V}$	15			

◆  **$h_{FE-1}$  Classifications**

R	Q	P	O
40-90	70-150	120-250	200-450